

What is claimed is:

1. A semiconductor device comprising a first film and a second film formed in contact with said first film, wherein a concentration of a contaminating impurity in an interface between said first film and said second film is  $2 \times 10^{16}$  atoms/cm<sup>3</sup> or less.

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2. A device according to claim 1, wherein the contaminating impurity is at least one element selected from periodic table group 1 elements or periodic table group 2 elements.

10 3. A device according to claim 1, wherein the contaminating impurity element is at least one element selected from the group consisting of Na, K, Mg, Ca, and Ba.

15 4. A device according to claim 1, wherein said first film and said second film are a crystalline semiconductor film and an insulating film in contact with the crystalline semiconductor film, respectively.

20 5. A device according to claim 1, wherein said first film and said second film are an insulating film functioning as a gate insulating film and a gate wiring in contact with the insulating film.

6. A semiconductor device comprising a first film, and a second film formed in contact with said first film, wherein a concentration of a contaminating impurity within said first film, a concentration of the contaminating impurity within said second film, and a concentration of the contaminating impurity in the interface between said first

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film and said second film are all  $2 \times 10^{16}$  atoms/cm<sup>3</sup> or less, respectively.

7. A device according to claim 6, wherein the contaminating impurity is at least one element selected from periodic table group 1 elements or periodic table group 2 elements.

8. A device according to claim 6, wherein the contaminating impurity element is at least one element selected from the group consisting of Na, K, Mg, Ca, and Ba.

9. A device according to claim 6, wherein said first film and said second film are a crystalline semiconductor film and an insulating film in contact with the crystalline semiconductor film, respectively.

10. A device according to claim 6, wherein said first film and said second film are an insulating film functioning as a gate insulating film and a gate wiring in contact with the insulating film.

11. A method of manufacturing a semiconductor device, comprising steps of:  
forming a first film;  
removing a contaminating impurity from the surface of the first film; and  
forming a second film in contact with the first film from the surface of which the contaminating impurity has been removed.

12. A method according to claim 11, wherein the contaminating impurity is at

least one element selected from periodic table group 1 elements or periodic table group 2 elements.

13. A method according to claim 11, wherein the contaminating impurity element  
5 is at least one element selected from the group consisting of Na, K, Mg, Ca, and  
Ba.

14. A method according to claim 11, wherein the contaminating impurity is  
removed by an acidic solution containing fluorine.

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